

**Selenium Insertion into the M–C Bond (M = Ga, In):
Syntheses and X-ray Crystal Structures of
[Np₂In(μ -SeNp)]₂, [(Me₃SiCH₂)₂Ga(μ -SeCH₂SiMe₃)]₂,
[(Mes)C₆H₇N·Ga- μ -Se]₂, and (Mes)₂C₆H₇N·GaSeMes (Np =
CH₂C(CH₃)₃, Mes = 2,4,6-Me₃C₆H₂, C₆H₇N = 4-Picoline)**

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The independent 1:1 reactions of InNp₃ (Np = CH₂CMe₃) and Ga(CH₂SiMe₃)₃ with elemental selenium resulted in the formation of novel dimeric compounds with the general formula [R₂M(μ -SeR)]₂ (M = In, R = Np (**1**); M = Ga, R = CH₂SiMe₃ (**2**)) in a nearly quantitative yield. Reaction of GaMes₃ (Mes = 2,4,6-Me₃C₆H₂) with 2 mol of elemental Se, and subsequent addition of 4-picoline (C₆H₇N), resulted in the isolation of three compounds, [(Mes)C₆H₇N·Ga- μ -Se]₂ (**3**), (Mes)₂C₆H₇N·GaSeMes (**4**), and Se₂Mes₂. Compound **3** is a selenium-bridged dimer with two two-coordinate Se atoms and two 4-picoline (C₆H₇N) molecules in the dimeric unit. In related work, reaction of InNp₃ with S₂Ph₂ afforded the dimeric compound [Np₂In(μ -SPh)]₂ (**5**) with elimination of NpSPh. The synthesis and characterization of **1–5**, including their solid-state structures, are presented.

Introduction

Unlike the chemistry of II–VI (12–16) compounds and the structural diversity that exists in such systems,^{1–7} the chemistry of III–VI (13–16) compounds and materials is in its infancy. Semiconducting materials such as GaS have been made by metal–organic chemical vapor deposition (MOCVD) using the single-source precursor [(^tBu)GaS]₄,^{8,9} and the cubic phase of GaS has been found to enhance the photoluminescence intensity of GaAs.¹⁰ Syntheses of mixed-metal chalcogenides such as CuInE₂ (E = S, Se) from a single-source precursor^{11,12} have been successful and their efficiency as photovoltaic cells are documented.^{13,14}

There are several methods of synthesizing organometallic 13–16 compounds that have been previously reported in the literature.^{15–18} However, there are only a handful of fully characterized compounds for the Ga–Se systems,^{19–22} whereas more examples could be found for the Al–S and Ga–S systems.²³ Herein, we report the synthesis and characterization of five novel compounds, [Np₂In(μ -SeNp)]₂ (Np = CH₂CMe₃) (**1**), [(Me₃SiCH₂)₂Ga(μ -SeCH₂SiMe₃)]₂ (Mes = 2,4,6-Me₃C₆H₂) (**2**), [(Mes)C₆H₇N·Ga- μ -Se]₂ (**3**), (Mes)₂C₆H₇N·GaSeMes (**4**), and [Np₂In(μ -SPh)]₂ (**5**).

Experimental Section

General Considerations. All manipulations of air- and moisture-sensitive materials were performed in a Vacuum Atmospheres HE-493 Dri-Lab containing an argon atmosphere and by general Schlenk techniques. Toluene and pentane were distilled over Na/K alloy.

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Elemental Se, S₂Ph₂, and 4-picoline (NC₆H₇) were purchased from Aldrich and were used as received. InNp₃,²⁴ Ga(CH₂-SiMe₃)₃,²⁵ and GaMe₃²⁶ were prepared according to the literature methods. ¹H and ¹³C{¹H} NMR spectra were recorded on a QE-300 spectrometer operating at 300 and 75.4 MHz, respectively. ¹H and ¹³C{¹H} NMR spectra were referenced to TMS by using the residual protons or carbons of deuterated benzene at δ 7.15 or 128 ppm, respectively, and the upfield pentet of C₇D₈ at δ 2.09 ppm for the ¹H NMR spectra and δ 20.4 ppm for ¹³C{¹H} NMR spectra. All NMR samples were prepared in 5-mm tubes, which were septum-sealed under argon. Melting points (uncorrected) were obtained with a Thomas-Hoover Uni-melt apparatus, and capillaries were flame-sealed under argon. Elemental Analyses were performed by E + R Microanalytical Laboratory, Inc., Corona, NY. Mass spectral data were collected on a JEOL JMS-SX 102A spectrometer operating in the electron ionization mode at 20 eV. X-ray crystallographic data were obtained at 25 °C on a Siemens P4 diffractometer utilizing graphite-monochromated Mo K α (λ = 0.710 73 Å) radiation.

Preparation of [Np₂In(μ -SeNp)]₂ (1). Inside the Dri-Lab a 250 mL Schlenk flask equipped with a magnetic stirbar was charged with InNp₃ (1.00 g, 3.05 mmol) and ca. 25 mL of toluene. A 0.24 g (3.05 mmol) amount of Se was added to the solution, and the resulting mixture was refluxed. After 30 min, all the Se was consumed and a colorless solution was formed. The solution was allowed to reflux for 6 h to ensure complete reaction, after which all of the volatile materials were removed under *vacuo* and the resultant white residue was dissolved in 5 mL of pentane. The X-ray quality colorless crystals of **1** were deposited at the bottom of the flask at -30 °C. Yield: 90% based on Se. Mp: 156 °C. Anal. Calcd (found) for C₃₀H₆₆In₂Se₂: C, 44.24 (44.47); H, 8.17 (8.31). ¹H NMR (C₆D₆): δ 1.35 (18H, s, Se-CH₂CMe₃), 1.61 (36H, s, In-CH₂CMe₃), 1.85 (8H, s, In-CH₂CMe₃), 3.36 (4H, s, Se-CH₂-CMe₃). ¹³C{¹H} NMR (C₆D₆): δ 28.12 (Se-CH₂CMe₃), 31.09 (Se-CH₂CMe₃), 31.93 (In-CH₂CMe₃), 33.93 (In-CH₂CMe₃), 34.65 (Se-CH₂CMe₃), 36.62 (In-CH₂CMe₃). MS (EI mode): *m/e* 1064 ([M + ^M/₂] - (2Np + Me)⁺), 986 ([M + ^M/₂] - (2Np + Se)⁺), 743 ([M - Np]⁺), 408 ([^M/₂]⁺), 337 ([^M/₂ - Np]⁺), 257 ([InNp₂]⁺), 114.9 ([In]⁺).

Preparation of [(Me₃SiCH₂)₂Ga(μ -SeCH₂SiMe₃)]₂ (2). Compound **2** was synthesized using a procedure similar to that used for **1**. Note: Reaction time was 24 h. Reactants: Ga-(CH₂SiMe₃)₃ (0.50 g, 1.51 mmol), Se (0.12 g, 1.51 mmol). Yield: 0.67 g, 94% based on Se. Mp: 106 °C. Anal. Calcd (found) for C₂₄H₆₆Ga₂Se₂Si₆: C, 35.13 (35.19); H, 8.11 (8.07). ¹H NMR: δ 0.10 (18H, s, Se-CH₂SiMe₃), 0.27 (36H, s, Ga-CH₂SiMe₃), 0.15 (8H, s, Ga-CH₂SiMe₃), 1.91 (4H, s, Se-CH₂-SiMe₃). ¹³C{¹H} NMR (C₆D₆): δ -1.29 (Se-CH₂SiMe₃), 2.19 (Ga-CH₂SiMe₃), 2.54 (Ga-CH₂SiMe₃), 5.38 (Se-CH₂SiMe₃). MS (EI mode): *m/e* 735 ([M - CH₂SiMe₃]⁺), 441 ([^M/₂]⁺), 395 ([^M/₂ - Me]⁺), 323 ([SeGa(CH₂SiMe₃)₂]⁺), 244 ([Ga(CH₂-SiMe₃)₂]⁺).

Preparation of [(Mes)C₆H₇N-Ga- μ -Se]₂ (3) and (Mes)₂-C₆H₇N-GaSeMes (4). Inside the Dri-Lab 3.15 g (7.37 mmol) of GaMe₃ and 0.52 g (7.37 mmol) of Se were combined in a 250 mL Schlenk flask, and ca. 100 mL of toluene was added to the mixture. The flask was removed from the Dri-Lab, and the resultant mixture was refluxed for 24 h. After 20 min of refluxing, the color of the solution had changed to yellow and after 2 h all of the selenium was consumed. A second mole of selenium (0.52 g) was added to the homogeneous light orange solution, and the mixture was refluxed for another 24 h. At the end of this period, a white solid had precipitated out of the solution with the consumption of all the selenium. To this

solution was added 1.44 mL (14.74 mmol) of 4-picoline *via* syringe in ca. 10 min while stirring the solution. The solution was then heated with a heat gun to dissolve all of the precipitate. The flask was left undisturbed overnight at room temperature, and the X-ray quality crystals of **3** were deposited at the bottom of the flask. The solution was separated from the crystals of **3**, and the solution was cooled to -20 °C to afford a powder which was identified as **4**. Recrystallization of the powder from toluene afforded the X-ray quality crystals of **4**.

Data for 3: Yield 0.96 g, 81% based on Se. Mp: >300 °C (dec). Anal. Calcd (found) for C₃₀H₃₆Ga₂N₂Se₂: C, 49.91 (49.88); H, 5.03 (5.15); N, 3.88 (3.92). ¹H NMR (C₆D₆): δ 1.47 (6H, s, 4-CH₃-pyridine), 2.22 (6H, s, *p*-Me of Mes), 3.02 (12H, s, *o*-Me of Mes), 6.17 (4H, d, *J*_{H-H} = 4.2 Hz, *m*-H of 4-picoline), 6.92 (4H, s, *m*-H of Mes), 8.88 (4H, d, *J*_{H-H} = 4.5 Hz, *o*-H of 4-picoline). ¹³C{¹H} NMR (C₆D₆): δ 20.56 (Me-pyridine), 21.27 (*p*-Me of Mes), 25.84 (*o*-Me of Mes), 125.52, 127.31, 128.56, 137.73, 146.23, 147.50 (aryl). MS (EI mode): *m/e* 307 ([GaMe₂]⁺).

Data for 4: Yield 1.52 g, 77% based on Se. Mp: 179 °C. Anal. Calcd (found) for C₃₃H₄₀GaNSe: C, 66.13 (66.02); H, 6.73 (6.82); N, 2.34 (2.25). ¹H NMR (C₆D₆): δ 1.47 (3H, s, 4-CH₃-pyridine), 2.10 (3H, s, *p*-Me of Mes-Se), 2.16 (6H, s, *p*-Me of Mes-Ga), 2.39 (12H, s, *o*-Me of Mes-Ga), 2.53 (6H, s, *o*-Me of Mes-Se), 6.16 (2H, d, *J*_{H-H} = 3.6 Hz, *m*-H of 4-picoline), 6.72 (2H, s, *m*-H of Mes-Se), 6.77 (4H, s, *m*-H of Mes-Ga), 8.70 (4H, b, *o*-H of 4-picoline). ¹³C{¹H} NMR (C₆D₆): δ 20.59 (Me-pyridine), 20.93 (*p*-Me of Mes-Se), 21.14 (*p*-Me of Mes-Ga), 25.76 (*o*-Me of Mes-Ga), 26.41 (*o*-Me of Mes-Se), 125.48, 130.96, 134.65, 136.95, 143.70, 143.32, 144.39, 144.89, 145.64, 148.55, 151.63 (aryl). MS (EI mode): *m/e* 666 ([M + Se]⁺), 586 ([M = C₃₃H₄₀GaNSe]⁺), 467 ([M - Mes]⁺), 398 ([Se₂Me₂]⁺), 318 ([MesSeMes]⁺), 200 ([HSeMes]⁺), 120 ([MesH]⁺).

Preparation of [Np₂In(μ -SePh)]₂ (5). A 0.33 g (1.01 mmol) amount of InNp₃ and 0.22 g (1.01 mmol) of S₂Ph₂ were combined in a Schlenk flask equipped with a magnetic stirbar. Pentane (20 mL) was added to the mixture, and the resultant clear solution was stirred for 12 h. The volume of pentane was reduced to 5 mL *in vacuo*, and the X-ray quality colorless crystals of **5** were deposited at the bottom of the flask at -30 °C. Yield: 89% based on InNp₃. Mp: 83 °C. Anal. Calcd (found) for C₃₂H₅₄In₂S₂: C, 52.47 (52.54); H, 7.43 (7.60). ¹H NMR (C₆D₆): δ 1.61 (36H, s, In-CH₂CMe₃), 1.85 (8H, s, In-CH₂CMe₃), 7.01 (6H, m, *m*, *p*-H of Ph), 7.59 (4H, d, *o*-H of Ph). ¹³C{¹H} NMR (C₆D₆): δ 32.71 (In-CH₂CMe₃), 34.90 (In-CH₂CMe₃), 40.66 (In-CH₂CMe₃), 126.20, 128.98, 133.69, 134.14 (aryl). MS (EI mode): *m/e* 699 ([M - S]⁺), 661 ([M - Np]⁺), 366 ([^M/₂]⁺), 295 ([^M/₂ - Np]⁺), 258 ([InNp₂]⁺), 324.

X-ray Structural Solution and Refinement. Crystal, data collection, and refinement parameters are given in Table 1. Suitable crystals of **1**–**5** were mounted in thin-walled capillaries and temporarily sealed with silicone grease under an argon atmosphere and then flame-sealed.

Preliminary photographic data indicated a primitive monoclinic crystal system for **1**, **4**, and **5**, an *I*-centered monoclinic system for **3**, and no symmetry higher than triclinic for **2**. The systematic absences in the diffraction data for **1**, **4**, and **5** are uniquely consistent with the reported space groups for **1**, **4**, and **5**. The centrosymmetric options were chosen for **2** and **3** which yielded chemically reasonable and computationally stable results of refinement.

The structures were solved using direct methods, completed by subsequent difference Fourier syntheses, and refined by full-matrix least-squares procedures. Semi-empirical ellipsoid absorption corrections were applied to **2** and **5** but not for **1**, **3**, and **4** because there was less than 10% variation observed in the ψ -scan data. The molecules of **1** and **3** are located on an inversion center, and **2** contains two independent but chemically equivalent molecules, each lying on an inversion center. All non-hydrogen atoms were refined with anisotropic displacement coefficients, and hydrogen atoms were treated

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Table 1. Crystal Data and Structure Refinement for [Np₂In(μ-SeNp)]₂ (**1**), [(Me₃SiCH₂)₂Ga(μ-Se(CH₂SiMe₃))]₂ (**2**), [(Mes)₂C₆H₇N·Ga-μ-Se]₂ (**3**), (Mes)₂C₆H₇N·GaSeMes (**4**), [Np₂In(μ-SPh)]₂ (**5**) (Np = CH₂C(CH₃)₃, Mes = 2,4,6-(CH₃)₃C₆H₂)

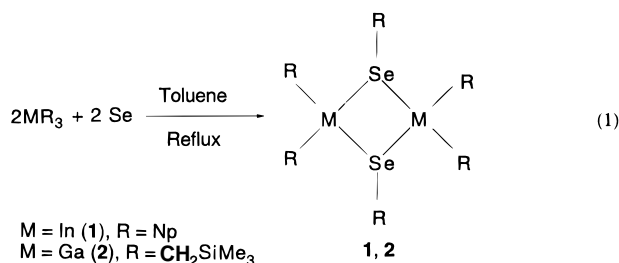
	1	2	3	4	5
empirical formula	C ₃₀ H ₆₆ In ₂ Se ₂	C ₂₄ H ₆₆ Ga ₂ Se ₂ Si ₆	C ₃₀ H ₃₆ Ga ₂ N ₂ Se ₂	C ₃₃ H ₄₀ GaNSe	C ₃₂ H ₅₄ In ₂ S ₂
fw	814.39	820.67	721.97	599.34	732.51
temp, K	233(2)	233(2)	298(2)	298(2)	237(2)
radiation (wavelength, Å)	Mo Kα (0.710 73)	Mo Kα (0.710 73)	Mo Kα (0.710 73)	Mo Kα (0.710 73)	Mo Kα (0.710 73)
space group	P2 ₁ /c	P1	I2/a	I2 ₁ /n	P2 ₁ /c
a, Å	10.241(2)	10.058(2)	14.771(2)	14.080(2)	18.778(3)
b, Å	10.393(3)	11.506(2)	13.336(1)	15.413(1)	10.050(1)
c, Å	18.501(4)	19.826(4)	15.924(2)	14.577(1)	19.880(2)
α, deg		82.44(1)			
β, deg	102.25(2)	89.80(2)	99.187(8)	108.186(8)	104.31(1)
γ, deg		73.49(1)			
V, Å ³	1924.3(3)	2179.4(7)	3096.8(6)	3005.4(5)	3635.4(6)
D _{calcd} , g cm ⁻³	1.406	1.251	1.549	1.325	1.338
Z	2	2	4	4	4
abs coeff cm ⁻¹	31.04	30.83	41.11	21.47	14.00
cryst dimens mm	0.30 × 0.20 × 0.20	0.40 × 0.25 × 0.15	0.40 × 0.10 × 0.10	0.40 × 0.30 × 0.30	0.40 × 0.40 × 0.25
cryst habit	colorless block	colorless block	colorless rod	colorless block	colorless block
q range for data collection, deg	2.11–21.49	2.01–22.50	2.00–22.49	2.02–22.49	2.11–33.50
no. of rflns collected	3014	6845	2447	4819	5985
no. of independent rflns	2196 (<i>R</i> _{int} = 0.0254)	5677 (<i>R</i> _{int} = 0.0469)	2009 (<i>R</i> _{int} = 0.0617)	3876 (<i>R</i> _{int} = 0.0677)	4750 (<i>R</i> _{int} = 0.0393)
goodness-of-fit on <i>F</i> ²	1.173	1.498	1.237	1.008	1.313
final <i>R</i> indices ^a [<i>I</i> > 2σ(<i>I</i>)]	<i>R</i> 1 = 0.0491 w <i>R</i> 2 = 0.1039	<i>R</i> 1 = 0.0627 w <i>R</i> 2 = 0.1441	<i>R</i> 1 = 0.0457 w <i>R</i> 2 = 0.1035	<i>R</i> 1 = 0.0460 w <i>R</i> 2 = 0.0914	<i>R</i> 1 = 0.0397 w <i>R</i> 2 = 0.0939

^a Quantity minimized = $R = \sum \Delta / \sum (F_o)$, $\Delta = -|F_o - F_c|$; $R(wF^2) = \sum [w(F_o^2 - F_c^2)^2] / \sum [(wF_o^2)^2]^{1/2}$.

as idealized contributions. All software and sources of the scattering factors are contained in the SHELXTL(5.3) program libraries.²⁷

Results and Discussion

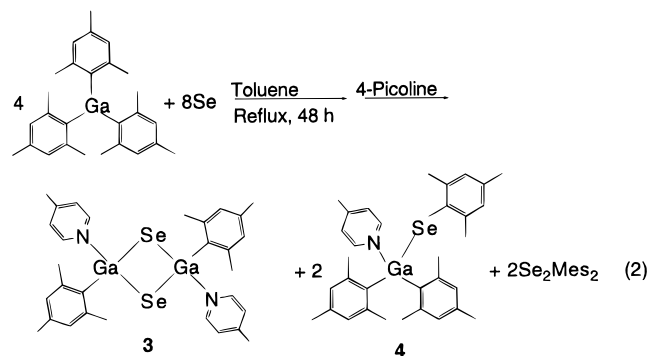
Syntheses. Independent reactions of InNp₃ (Np = CH₂C(CH₃)₃) and Ga(CH₂SiMe₃)₃ with elemental selenium in a 1:1 ratio in refluxing toluene resulted in the formation of [Np₂In(μ-SeNp)]₂ (**1**) and [(Me₃SiCH₂)₂Ga(μ-Se(CH₂SiMe₃))]₂ (**2**) in nearly quantitative yields (eq 1). In the formation of **1**, all of the selenium is



consumed within 1/2 h, whereas for compound **2** the elemental selenium was consumed over the course of several hours under similar conditions.

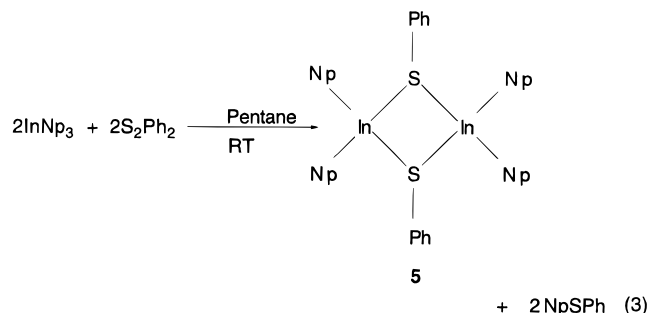
The reaction of GaMes₃ with 2 mol of elemental Se resulted in the formation of a precipitate which was insoluble in toluene. We did not attempt to isolate and characterize the white precipitate, however, upon molar addition of the base, 4-picoline (C₆H₇N), to the original reaction flask and heating the reaction mixture, all of the precipitate was dissolved to form a homogeneous orange solution. Leaving the flask undisturbed at room temperature for several hours resulted in the formation of X-ray quality crystals (colorless rods) of **3**. X-ray quality crystals (colorless blocks) of **4** were isolated from recrystallization of a white powder obtained from the

original orange solution at –20 °C. Inside the Dri-Lab the orange solution was evaporated to leave an orange residue, which was completely dissolved in pentane. The pentane solution yielded crystals (golden blocks) which were identified by ¹H NMR and MS data to be Se₂Mes₂ (eq 2). The white insoluble precipitate, from which



compounds **3** and **4** were isolated, could have consisted of the large aggregate (MesGaSe)_n as well as (Mes₂GaSeMes)_n, which upon addition of the base (C₆H₇N) yielded the more soluble adducts (eq 2).

Compound **5** was synthesized according to eq 3 (*vide infra*), with the byproduct NpSPh being identified by GC/MS. The formation of [Np₂In(μ-SPh)]₂ and NpSPh



(27) SHELXTL PC; Siemens Analytical X-ray Instruments, Inc.: Madison, WI, 1990.

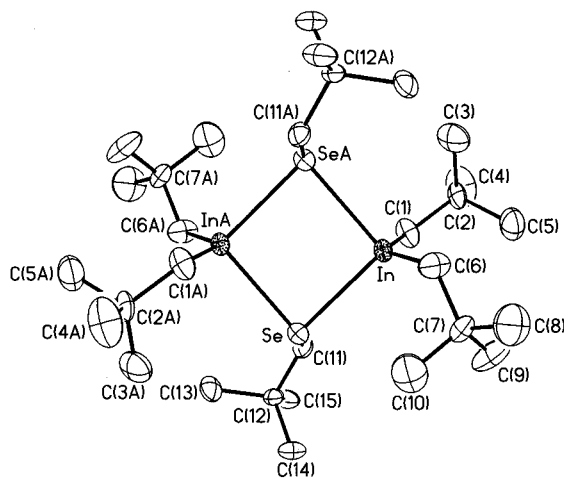


Figure 1. Molecular diagram (30% probability ellipsoids) showing the solid-state structure and atom-numbering scheme of $[\text{Np}_2\text{In}(\mu\text{-SeNp})]_2$ (**1**).

suggest that the reaction mechanism is similar to the reactions of InMe_3 with diselenides and ditellurides reported earlier.^{20,28,29}

Compounds **1**, **2**, and **5** are extremely soluble in pentane, whereas **3** is slightly soluble and **4** shows better solubility in toluene. Compounds **1–5** are air sensitive and decomposed slowly in the presence of air.

We have observed that the independent insertion reactions of GaR_3 and elemental Se are much slower when compared to similar reactions with InR_3 and elemental Se under similar forcing conditions, keeping in mind the similar bulk of the R groups. This behavior is also observed by Uhl and co-workers.²¹ One explanation might be that when we compare InR_3 to GaR_3 (R is a bulky group such as mesityl or neopentyl), the bulky substituent can offer much more protection to the smaller Ga center making it a much more hindered molecule and, therefore, less reactive toward Se insertion.

Spectroscopic Studies. The mass spectrum of **1** shows larger fragments than the dimeric unit observed in the solid state, suggesting the existence of a larger aggregate in the vapor phase. Compounds **1**, **2**, and **4** are reasonably volatile and their mass spectra show isotope patterns that match with the calculated isotope patterns well.

The ^1H NMR spectrum of **4** shows two sharp doublets for the *ortho* and *meta* protons on the picoline group, whereas in compound **5** these signals are much broader, suggesting an exchange process in solution.³⁰ Variable-temperature NMR studies (-85 to 80°C) were carried out for compounds **2**, **3**, and **5** but no significant changes were observed.

Structures of $[\text{Np}_2\text{In}(\mu\text{-SeNp})]_2$ (1**) and $[(\text{Me}_3\text{SiCH}_2)_2\text{Ga}(\mu\text{-SeCH}_2\text{SiMe}_3)]_2$ (**2**).** Thermal ellipsoid diagrams of **1–5** are shown in Figures 1–6. Crystal data and structure refinement for **1–5** are given in Table 1. Selected interatomic bond distances and bond angles for **1–5** are presented in Tables 2–6. Compounds **1** and **2** have a central $(\text{MSe})_2$ core with the substituent on the Se in the *anti* conformation, with this

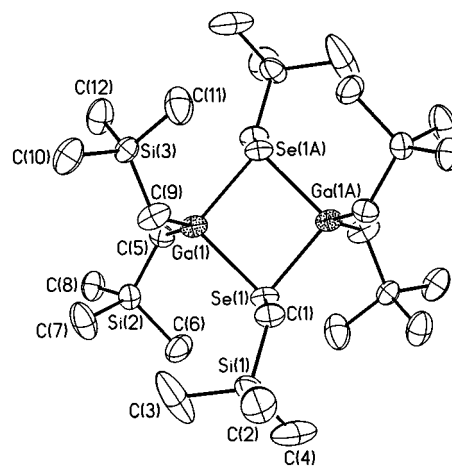


Figure 2. Molecular diagram (30% probability ellipsoids) showing the solid-state structure and atom-numbering scheme of $[(\text{Me}_3\text{SiCH}_2)_2\text{Ga}(\mu\text{-Se}(\text{CH}_2\text{SiMe}_3)_2)]_2$ (molecule **1**) (**2**). Hydrogen atoms are omitted for clarity.

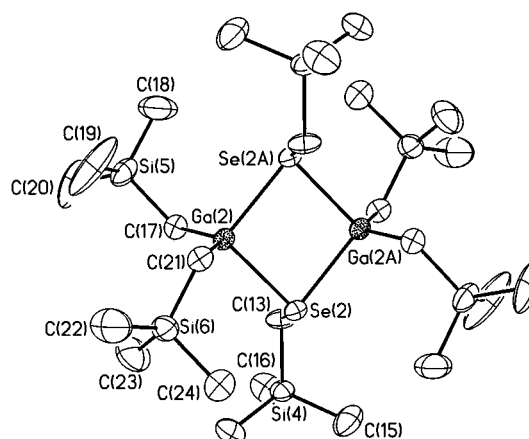


Figure 3. Molecular diagram (30% probability ellipsoids) showing the solid-state structure and atom-numbering scheme of $[(\text{Me}_3\text{SiCH}_2)_2\text{Ga}(\mu\text{-Se}(\text{CH}_2\text{SiMe}_3)_2)]_2$ (molecule **2**) (**2**). Hydrogen atoms are omitted for clarity.

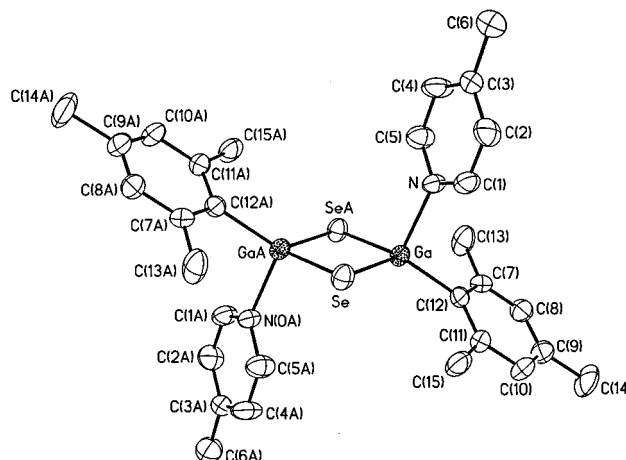


Figure 4. Molecular diagram (30% probability ellipsoids) showing the solid-state structure and atom-numbering scheme of $[(\text{Mes})_6\text{H}_7\text{N-Ga-}\mu\text{-Se}]_2$ (**3**). Hydrogen atoms are omitted for clarity.

orientation of ligands presumably minimizing the steric interaction. Both compounds possess a planar four-membered ring and the metal centers have to quasi-tetrahedral geometry. A planar core is found in $[\text{Me}_2\text{-In}(\mu\text{-Cl})]_2$,³¹ however, a folded conformation is reported

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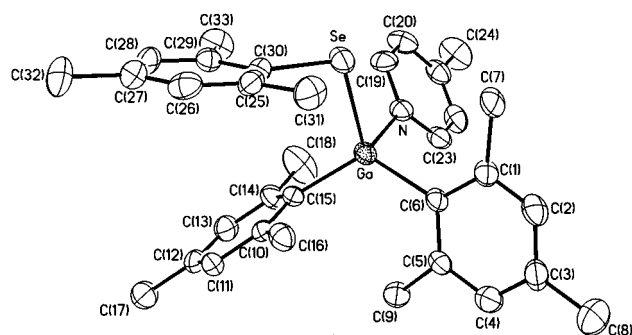


Figure 5. Molecular diagram (30% probability ellipsoids) showing the solid-state structure and atom-numbering scheme of $(\text{Mes})_2\text{C}_6\text{H}_7\text{N}\cdot\text{GaSeMes}$ (**4**). Hydrogen atoms are omitted for clarity.

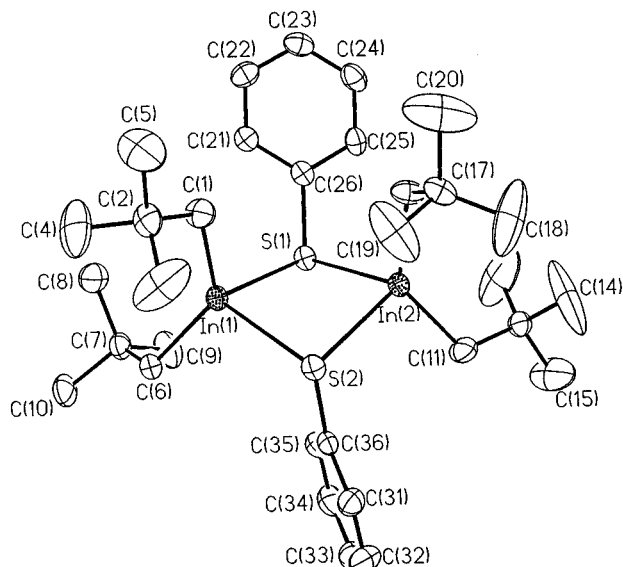


Figure 6. Molecular diagram (30% probability ellipsoids) showing the solid-state structure and atom-numbering scheme of $[\text{Np}_2\text{In}(\mu\text{-SePh})]_2$ (**5**). Hydrogen atoms are omitted for clarity.

Table 2. Selected Bond Distances (Å) and Bond Angles (deg) for $[\text{Np}_2\text{In}(\mu\text{-SeNp})]_2$ (1**), with Estimated Standard Deviations in Parentheses^a**

Bond Lengths			
In–C(1)	2.197(11)	In–C(6)	2.198(9)
In–Se	2.7053(14)	In–SeA	2.719(2)
Se–C(11)	1.972(10)	Se–InA	2.719(2)
C(1)–C(2)	1.50(2)	C(2)–C(3)	1.51(2)
Bond Angles			
C(6)–In–C(1)	134.5(4)	C(6)–In–Se	109.1(3)
C(1)–In–Se	104.2(3)	C(6)–In–SeA	107.5(4)
C(1)–In–SeA	99.9(3)	Se–In–SeA	94.06(4)
C(11)–Se–In	103.1(3)	C(11)–Se–InA	108.1(3)
In–Se–InA	85.94(4)	C(2)–C(1)–In	118.4(7)

^a Symmetry transformation used to generate equivalent atoms: $-x, -y + 2, -z + 2$.

for $[\text{Np}_2\text{In}(\mu\text{-SePh})]_2$,³² $[\text{Mes}_2\text{In}(\mu\text{-I})]_2$,³³ and $\text{Np}_2\text{In}(\mu\text{-SePh})(\mu\text{-P}^t\text{Bu}_2)\text{InNp}_2$.³⁴ The In–Se bond lengths in **1** (average 2.71 Å) are comparable with those seen in $[\text{Mes}_2\text{In}(\mu\text{-SePh})]_2$ (average 2.732 Å),²⁹ $[\text{Mes}_2\text{In}(\mu\text{-SeMes})]_2$

Table 3. Selected Bond Distances (Å) and Bond Angles (deg) for $[(\text{Me}_3\text{SiCH}_2)_2\text{Ga}(\mu\text{-Se}(\text{CH}_2\text{SiMe}_3))_2]$ (2**) (Molecule **1** and **2**), with Estimated Standard Deviations in Parentheses^a**

Bond Lengths			
Se(1)–C(1)	1.983(9)	Se(1)–Ga(1)	2.523(2)
Se(1)–Ga(1A)	2.539(2)	Se(2)–C(13)	1.978(9)
Se(2)–Ga(2A)	2.529(2)	Se(2)–Ga(2)	2.5329(14)
Ga(1)–C(5)	1.959(9)	Ga(1)–C(9)	1.975(9)
Ga(1)–Se(1A)	2.539(2)	Ga(2)–C(21)	1.954(9)
Ga(2)–C(17)	1.961(9)	Ga(2)–Se(2A)	2.529(2)
Si(1)–C(2)	1.856(12)	Si(1)–C(1)	1.865(10)
Si(1)–C(4)	1.880(13)	Si(1)–C(3)	1.884(14)
N(1)–C(9)	1.468(3)	C(15)–C(20)	1.388(4)
Bond Angles			
C(1)–Se(1)–Ga(1)	105.3(3)	C(1)–Se(1)–Ga(1A)	102.4(3)
Ga(1)–Se(1)–Ga(1A)	85.35(5)	C(13)–Se(2)–Ga(2A)	102.9(3)
C(13)–Se(2)–Ga(2)	103.5(3)	Ga(2A)–Se(2)–Ga(2)	84.14(5)
C(5)–Ga(1)–C(9)	125.1(5)	C(5)–Ga(1)–Se(1)	107.5(3)
C(9)–Ga(1)–Se(1)	110.8(3)	C(5)–Ga(1)–Se(1A)	106.4(3)
C(9)–Ga(1)–Se(1A)	108.1(4)	Se(1)–Ga(1)–Se(1A)	94.65(5)
C(21)–Ga(2)–C(17)	125.6(4)	C(21)–Ga(2)–Se(2A)	109.7(3)
C(17)–Ga(2)–Se(2A)	106.7(3)	C(21)–Ga(2)–Se(2)	106.0(3)
C(17)–Ga(2)–Se(2)	108.9(2)	Se(2B)–Ga(2)–Se(2)	95.86(5)
C(2)–Si(1)–C(1)	107.8(6)	C(2)–Si(1)–C(4)	111.3(6)
C(1)–Si(1)–C(4)	108.0(6)	C(2)–Si(1)–C(3)	108.1(7)
Si(1)–C(1)–Se(1)	111.5(5)	Si(2)–C(5)–Ga(1)	121.0(5)
Si(3)–C(9)–Ga(1)	120.6(5)	Si(4)–C(13)–Se(2)	112.2(5)
Si(5)–C(17)–Ga(2)	118.8(4)	Si(6)–C(21)–Ga(2)	118.6(5)

^a Symmetry transformation used to generate equivalent atoms: 1A $-x + 2, -y, -z + 1$; 2A $-x - 1, -y + 3, -z$.

Table 4. Selected Bond Distances (Å) and Bond Angles (deg) for $[(\text{Mes})_2\text{C}_6\text{H}_7\text{N}\cdot\text{Ga}\mu\text{-Se}]_2$ (3**), with Estimated Standard Deviations in Parentheses^a**

Bond Lengths			
Se–Ga(1A)	2.3784(12)	Se–Ga	2.3872(13)
Ga–C(12)	1.988(7)	Ga–N	2.090(6)
Ga–Se(A)	2.3784(12)	N–C(1)	1.306(10)
N–C(5)	1.313(10)	C(1)–C(2)	1.382(11)
Bond Angles			
Ga(A)–Se–Ga	79.87(4)	C(12)–Ga–N	103.3(3)
C(12)–Ga–Se(A)	120.5(2)	N–Ga–Se(A)	104.7(2)
C(12)–Ga–Se	125.2(2)	N–Ga–Se	99.6(2)
Se(A)–Ga–Se	100.13(4)	C(1)–N–C(5)	116.8(7)
C(1)–N–Ga	118.6(6)	C(5)–N–Ga	123.9(6)
N–C(1)–C(2)	121.9(8)	C(3)–C(2)–C(1)	122.3(9)

^a Symmetry transformation used to generate equivalent atoms: $-x + 1, -y, -z + 1$.

Table 5. Selected Bond Distances (Å) and Bond Angles (deg) for $(\text{Mes})_2\text{C}_6\text{H}_7\text{N}\cdot\text{GaSeMes}$ (4**), with Estimated Standard Deviations in Parentheses^a**

Bond Lengths			
Se–C(30)	1.922(6)	Se–Ga	2.4383(9)
Ga–C(15)	2.004(5)	Ga–C(6)	2.004(6)
Ga–N	2.095(5)	C(1)–C(2)	1.384(8)
N–C(23)	1.347(7)	C(14)–C(18)	1.500(9)
Bond Angles			
C(30)–Se–Ga	106.7(2)	C(15)–Ga–C(6)	119.9(2)
C(15)–Ga–N	112.5(2)	C(6)–Ga–N	100.0(2)
C(15)–Ga–Se	111.3(2)	C(6)–Ga–Se	114.8(2)
N–Ga–Se	94.84(14)	C(1)–C(6)–Ga	122.5(5)
C(5)–C(6)–Ga	120.8(4)	C(10)–C(15)–Ga	117.3(4)
C(14)–C(15)–Ga	125.7(5)	C(23)–N–Ga	117.6(4)
C(29)–C(30)–Se	121.5(5)	C(25)–C(30)–Se	117.9(5)

(average 2.715 Å),²⁹ $[\text{Np}_2\text{In}(\mu\text{-SePh})]_2$ (average 2.743 Å),³² $[\text{P}^t\text{Bu}_2\text{In}(\mu\text{-Se}^t\text{Bu})]_2$ (2.70 Å),³⁵ and polymeric $[\text{In}(\text{SePh})_3]_\infty$ (average 2.78 Å)³⁶ but longer than those observed in polymeric $[\text{MeIn}(\text{SePh})(\mu\text{-SePh})]_\infty$ (bridging

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Table 6. Selected Bond Distances (Å) and Bond Angles (deg) for [Np₂In(μ-SPh)]₂ (5), with Estimated Standard Deviations in Parentheses^a

Bond Lengths			
In(1)–C(1)	2.162(6)	In(1)–C(6)	2.171(6)
In(1)–S(2)	2.618(2)	In(1)–S(1)	2.6318(14)
In(2)–C(16)	2.143(6)	In(2)–C(11)	2.155(6)
In(2)–S(2)	2.623(2)	In(1)–S(1)	2.651(2)
S(1)–C(26)	1.788(6)	S(2)–C(36)	1.783(6)
C(1)–C(2)	1.518(8)	C(2)–C(4)	1.521(12)
Bond Angles			
C(1)–In(1)–C(6)	131.7(2)	C(1)–In(1)–S(2)	101.2(2)
C(6)–In(1)–S(2)	108.8(2)	C(1)–In(1)–S(1)	105.6(2)
C(6)–In(1)–S(1)	112.4(2)	S(2)–In(1)–S(1)	87.48(5)
C(16)–In(2)–C(11)	136.3(3)	C(16)–In(2)–S(2)	108.1(2)
C(11)–In(2)–S(2)	103.9(2)	C(16)–In(2)–S(1)	103.1(2)
C(11)–In(2)–S(1)	107.5(2)	S(2)–In(2)–S(1)	86.98(5)
C(26)–S(1)–In(1)	110.0(2)	C(26)–S(1)–In(2)	106.3(2)
In(1)–S(1)–In(2)	88.25(5)	C(36)–S(2)–In(1)	110.2(2)
C(36)–S(2)–In(2)	102.3(2)	In(1)–S(2)–In(2)	89.14(5)
C(2)–C(1)–In(1)	119.2(5)	C(3)–C(2)–C(4)	108.5(9)

SePh 2.682 Å and terminal SePh 2.541 Å),²⁹ [In₂Se₂₁]^{4–} (average 2.67 Å),³⁷ In[SeC(SiMe₃)₃]₃ (average 2.527 Å),³⁸ In(SiMe₃)₃ (Mes* = 2,4,6-^tBu₃-C₆H₂; average 2.505 Å),³⁹ Mes*In(SePh)₂ (2.526 and 2.551 Å),⁴⁰ and [Tp⁺Bu₂][–]InSe (Tp = tris(pyrazolyl)hydroborate) (In–Se = 2.376–(1) Å).⁴¹

Only a few examples of Ga–Se bond distances are found in the literature. For **2**, the average Ga–Se bond distance of 2.53 Å is comparable to that of [Ph₂Ga(μ-SeMe)]₂ (2.51 Å)²⁰ but slightly longer than those found in cubane [^tBuGaSe]₄ (2.48 Å),¹⁹ monomeric Ga(S-eMes*)₃ (average 2.324 Å),⁴² [(Mes)C₆H₇N·Ga-μ-Se]₂ (**3**) (average 2.383 Å), and (Mes)₂C₆H₇N·GaSeMes (**4**) (2.428 Å). The average M–C bond distances and exocyclic C–M–C angles for **1** and **2** are in accordance with those of similar structures reported in the literature.²³ The bridging Se atoms in **1** and **2** are three-coordinate and have pyramidal geometry (ΣSe = 297.14° for **1** and ΣSe1 = 293.05° for **2**).

Structures of [(Mes)C₆H₇N·Ga-μ-Se]₂ (3**) and (Mes)₂C₆H₇N·GaSeMes (**4**).** Compound **3** is dimeric with the central core consisting of planar (GaSe)₂. The selenium atoms are in the bridging position and are two-coordinate. The gallium atoms have a distorted tetrahedral geometry. The Ga–Se bond distance of 2.38 Å is shorter than the Ga–Se bond distance for **2** but similar to Ga–Se bond length in monomeric R₂Ga–Se–GaR₂ (R = CH(SiMe₃)₂; 2.34 Å).²¹ This is understandable since the coordination number for Se atom is two

in **3** rather than three for **2**. The Ga–Se bond length of 2.38 Å in **3** is almost identical to the covalent radii reported for Ga–Se (2.37 Å).⁴³

Compound **4** is a simple adduct with a distorted tetrahedral geometry around the Ga center. The Ga–Se bond length of 2.44 Å is longer than the bond length observed for **3** but comparable to the Ga–Se bond length reported for [^tBuGaSe]₄ (2.48 Å).¹⁹ The Ga–N bond lengths of 2.090(6) Å for **3** and 2.095(5) Å for **4** are normal, when compared to the several Ga–N adduct bond lengths reported in the literature.⁴⁴

Structure of [Np₂In(μ-SPh)]₂ (5**).** Compound **5** also has an *anti* conformer with a puckered core consisting of (InS)₂. This molecule possess no crystallographic symmetry. Crystals of **5** are isomorphous with previously reported dimeric compounds [Np₂In(μ-SePh)]₂³² and [Np₂Ga(μ-TePh)]₂.⁴⁵ The In–S bond distances in **5** range from 2.618(2) to 2.651(2) Å. These values are in close agreement with the bond lengths in [Mes₂In(μ-S^t-Bu)]₂ (average 2.62 Å),⁴⁶ [Me₂In(μ-SSiPh₃)]₃ (average 2.609 Å),⁴⁶ and [^tBu₂In(μ-S^tBu)]₂ (2.60 Å)³⁵ but slightly longer than the similar bond lengths reported for [Ph₂In(μ-SSn(C₆H₁₁))₃]₂ (average 2.551 Å),⁴⁷ [Mes₂In(μ-SSiPh₃)]₂ (average 2.498 Å),⁴⁶ and [Mes₂In(μ-S^tamy)]₂ (average 2.592 Å).⁴⁶ The overall geometry around the S atoms in **5** are also pyramidal (ΣS(1) = 304.6° and ΣS(2) = 301.6°).

Conclusion

From the previously reported data in the literature and the data gathered here, we can conclude that the insertion of elemental selenium into the Ga–C and In–C bonds can occur with relative ease to produce the seleno-derivatives of these metals in good yield, if the substituent on the metal is sufficiently bulky. However, the insertion of more than one Se atom needs further investigation.

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Supporting Information Available: Tables of crystal and X-ray data collection parameters, bond distances and angles, anisotropic thermal parameters for the non-hydrogen atoms, and atomic coordinates and isotropic thermal parameters for the hydrogen atoms (27 pages). Ordering information is given on any current masthead page.

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